

METHOD AND APPARATUS TO REMOTELY SENSE
THE TEMPERATURE OF A POWER SEMICONDUCTOR

ABSTRACT OF THE DISCLOSURE

Apparatus for indirectly sensing the temperature of a power MOS device comprising a power MOS device having a current sense circuit for sensing the current in the power MOS device, a circuit for producing a voltage related to the drain-source voltage of the power MOS device, a comparator coupled to receive at a first input the voltage related to the drain-source voltage of the power MOS device and at a second input a voltage related to the current in the power MOS device, the comparator generating an overtemperature protection signal when a predetermined inequality between the voltages at the first and second inputs to the comparator occurs.